



BUL1403ED

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- INTEGRATED ANTISATURATION AND PROTECTION NETWORK
- INTEGRATED ANTIPARALLEL COLLECTOR EMITTER DIODE
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- ARCING TEST SELF PROTECTED

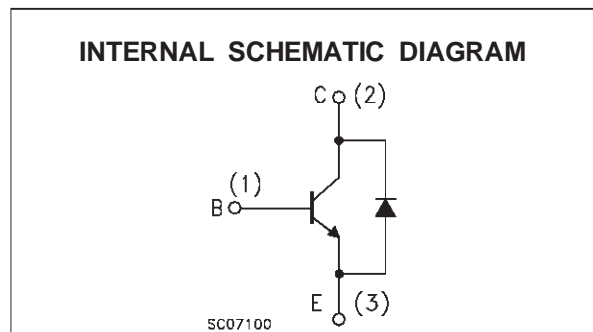
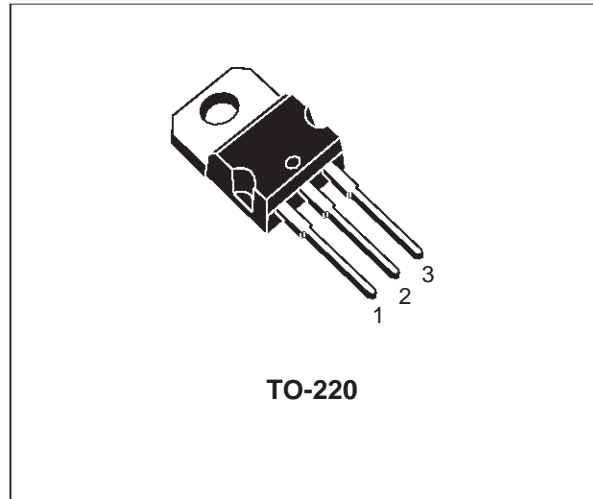
APPLICATIONS

- 2/4 LAMPS ELECTRONIC BALLAST FOR FLUORESCENT LIGHTING 277 V_{AC} PUSH-PULL CONFIGURATION

DESCRIPTION

The BUL1403ED is a new device, designed for fluorescent electronic ballast 277 V_{AC} push-pull applications (up to 4 lamps).

This device, it can be used without baker clamp and transil protection, reducing greatly the component count.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|---|------------|------|
| V _{CES} | Collector-Emitter Voltage (V _{BE} = 0) | 1400 | V |
| V _{CEO} | Collector-Emitter Voltage (I _B = 0) | 650 | V |
| V _{EBO} | Emitter-Base Voltage (I _C = 0) | 7 | V |
| I _C | Collector Current | 3 | A |
| I _{CM} | Collector Peak Current (t _p < 5 ms) | 6 | A |
| I _B | Base Current | 2 | A |
| I _{BM} | Base Peak Current (t _p < 5 ms) | 4 | A |
| P _{tot} | Total Dissipation at T _c = 25 °C | 80 | W |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

BUL1403ED

THERMAL DATA

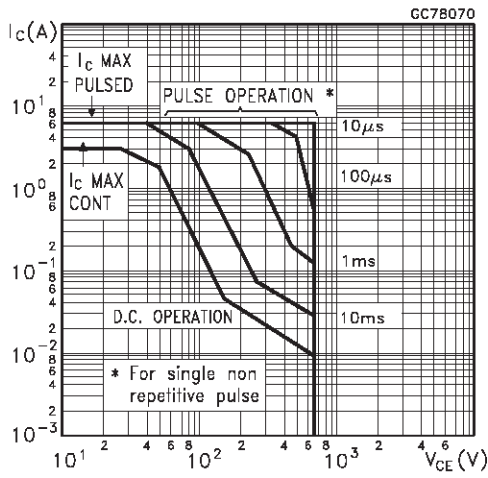
| | | | |
|-----------------------|--|------|------|
| R _{thj-case} | Thermal Resistance Junction-Case | 1.56 | °C/W |
| R _{thj-amb} | Max Thermal Resistance Junction-Ambient | 62.5 | °C/W |
| | Max | | |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

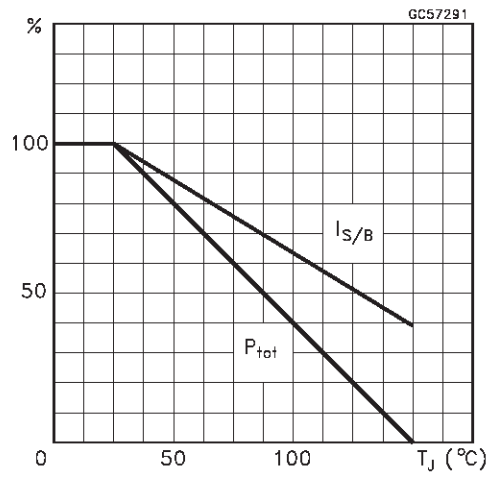
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--|--|--|---------------|------|---------------------------|----------------------|
| I _{CES} | Collector Cut-off Current (V _{BE} = 0) | V _{CE} = 1400 V | | | 1 | mA |
| I _{EBO} | Base-Emitter Leakage Current | V _{EB} = 7 V | | | 100 | μA |
| V _{CEO(sus)} | Collector-Emitter Sustaining Voltage (I _B = 0) | I _C = 10 mA L = 25 mH | 650 | | | V |
| V _{CE(sat)*} | Collector-Emitter Saturation Voltage | I _C = 0.5 A I _B = 0.05 A I _C = 0.25 A I _B = 0.025 A | | | 2.5 1.5 | V V |
| V _{BE(sat)*} | Base-Emitter Saturation Voltage | I _C = 0.5 A I _B = 0.1 A I _C = 1 A I _B = 0.1 A I _C = 2 A I _B = 0.4 A | | | 1.0 1.1 1.2 | V V V |
| h _{FE*} | DC Current Gain | I _C = 5 mA V _{CE} = 10 V I _C = 0.4 A V _{CE} = 3 V I _C = 0.8 A V _{CE} = 5 V | 18 15 4 | | | |
| t _d t _r t _s t _f | RESISTIVE LOAD Delay Time Rise Time Storage Time Fall Time | I _C = 0.5 A V _{CC} = 125 V I _{B1} = 0.05 A I _{B2} = -0.25 A D.C. = 2% P.W. = 300 μs | | | 0.3 0.8 1.2 0.35 | μs μs μs μs |
| E _{sb} | Repetitive Avalanche Energy | L = 2 mH | 6 | | | mJ |

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

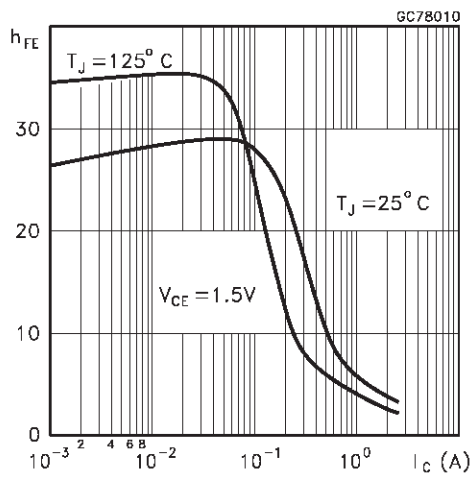
Safe Operating Areas



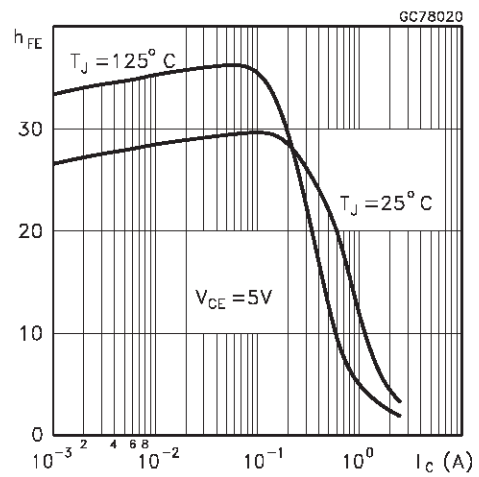
Derating Curve



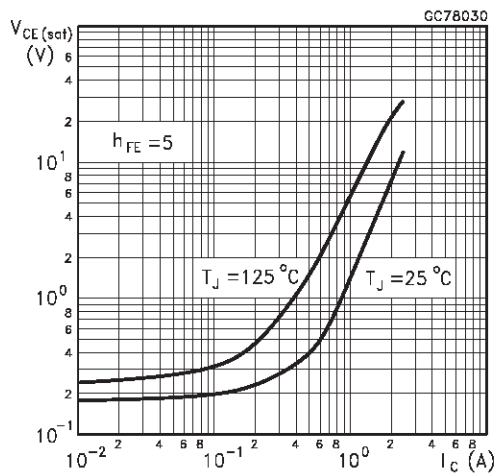
DC Current Gain



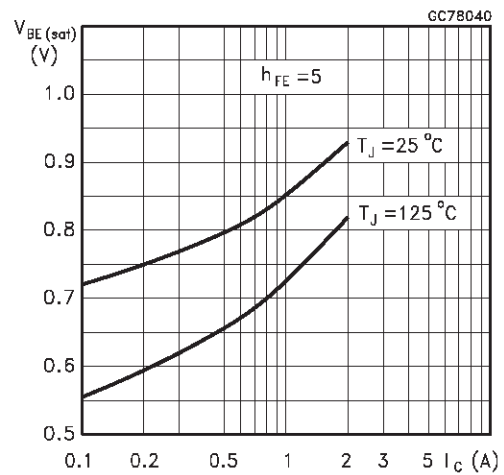
DC Current Gain



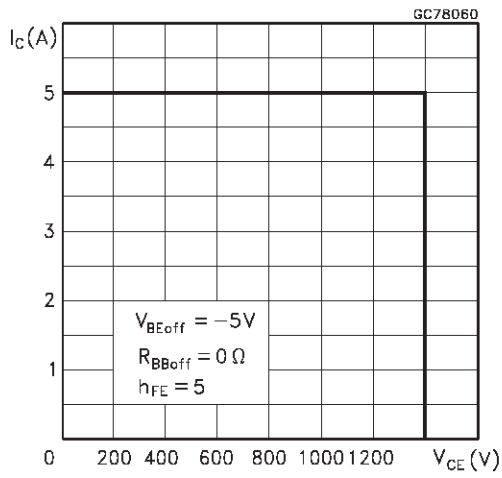
Collector Emitter Saturation Voltage



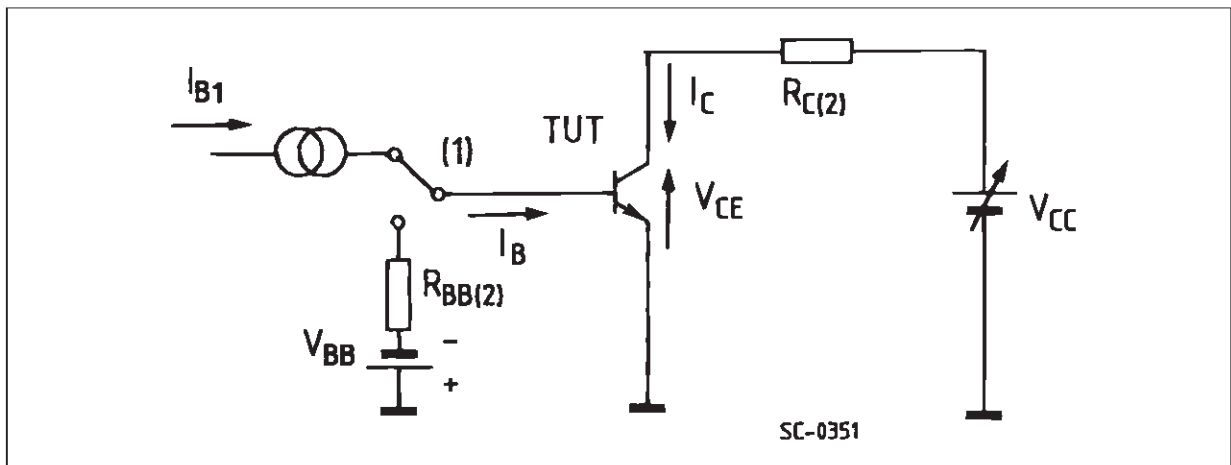
Base Emitter Saturation Voltage



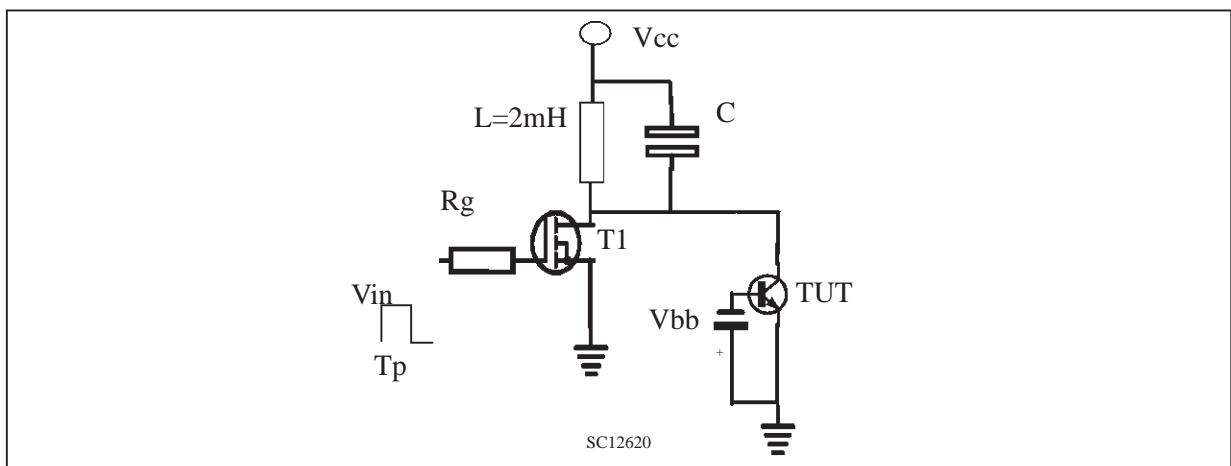
Reverse Biased SOA



Resistive Load Switching Test Circuit

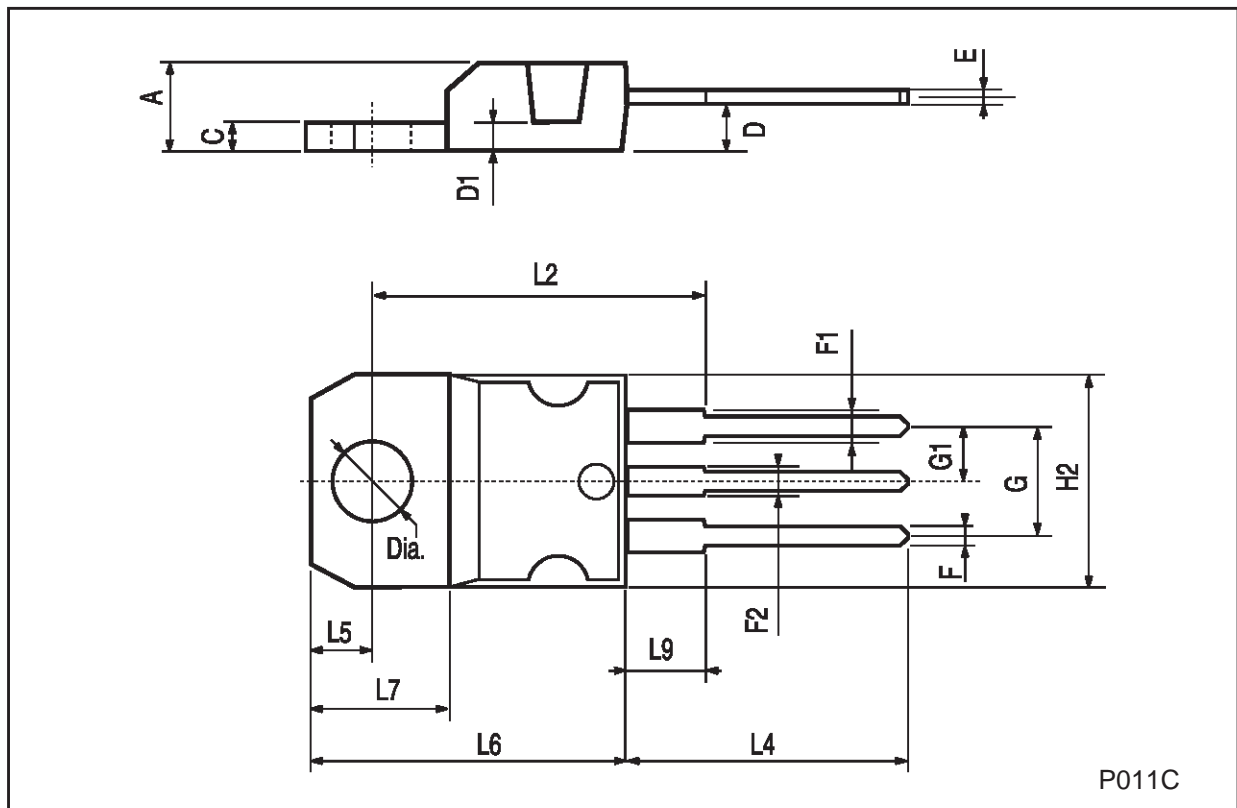


Energy Rating Test Circuit



TO-220 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| C | 1.23 | | 1.32 | 0.048 | | 0.051 |
| D | 2.40 | | 2.72 | 0.094 | | 0.107 |
| D1 | | 1.27 | | | 0.050 | |
| E | 0.49 | | 0.70 | 0.019 | | 0.027 |
| F | 0.61 | | 0.88 | 0.024 | | 0.034 |
| F1 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| F2 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| G | 4.95 | | 5.15 | 0.194 | | 0.203 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H2 | 10.0 | | 10.40 | 0.393 | | 0.409 |
| L2 | | 16.4 | | | 0.645 | |
| L4 | 13.0 | | 14.0 | 0.511 | | 0.551 |
| L5 | 2.65 | | 2.95 | 0.104 | | 0.116 |
| L6 | 15.25 | | 15.75 | 0.600 | | 0.620 |
| L7 | 6.2 | | 6.6 | 0.244 | | 0.260 |
| L9 | 3.5 | | 3.93 | 0.137 | | 0.154 |
| DIA. | 3.75 | | 3.85 | 0.147 | | 0.151 |



P011C

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